

THYRISTOR MODULE

PK(PD,PE)200HB

UL:E76102(M)

Power Thyristor/Diode Module PK200HB series are designed for various rectifier circuits and power controls. For your circuit application, following internal connections and wide voltage ratings up to 1,600V are available.

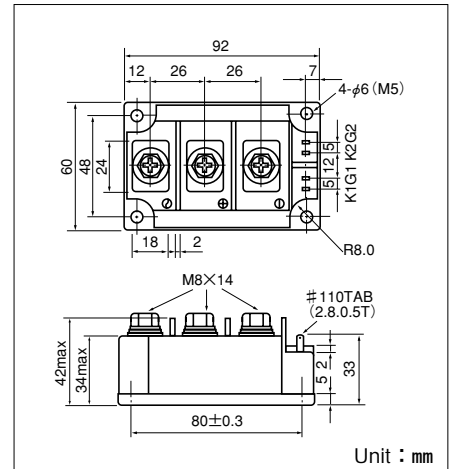
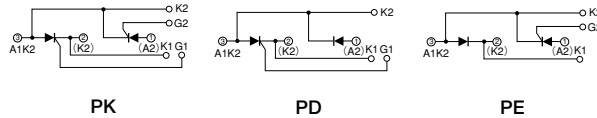
Isolated mounting base

- $I_{T(AV)}$ 200A, $I_{T(RMS)}$ 310A, I_{TSM} 5500A
- di/dt 200 A/ μ s
- dv/dt 500V/ μ s

(Applications)

- Various rectifiers
- AC/DC motor drives
- Heater controls
- Light dimmers
- Static switches

Internal Configurations



Maximum Ratings

Symbol	Item	Ratings		Unit	
		PK200HB120 PE200HB120	PD200HB120		PK200HB160 PE200HB160
V_{RRM}	* Repetitive Peak Reverse Voltage	1200		1600	V
V_{RSM}	* Non-Repetitive Peak Reverse Voltage	1300		1700	V
V_{DRM}	Repetitive Peak Off-State Voltage	1200		1600	V

Symbol	Item	Conditions	Ratings	Unit	
$I_{T(AV)}$	* Average On-State Current	Single phase, half wave, 180° conduction, $T_c : 74^\circ\text{C}$	200	A	
$I_{T(RMS)}$	* R.M.S. On-State Current	Single phase, half wave, 180° conduction, $T_c : 74^\circ\text{C}$	310	A	
I_{TSM}	* Surge On-State Current	1/2 cycle, 50Hz/60Hz, peak Value, non-repetitive	5000/5500	A	
I^2t	* I^2t	Value for one cycle of surge current	125000	A ² S	
P_{GM}	Peak Gate Power Dissipation		10	W	
$P_{G(AV)}$	Average Gate Power Dissipation		3	W	
I_{FGM}	Peak Gate Current		3	A	
V_{FGM}	Peak Gate Voltage (Forward)		10	V	
V_{RGM}	Peak Gate Voltage (Reverse)		5	V	
di/dt	Critical Rate of Rise of On-State Current	$I_G=100\text{mA}$, $T_j=25^\circ\text{C}$, $V_D=1/2V_{DRM}$, $dI_G/dt=0.1\text{A}/\mu\text{s}$	200	A/ μ s	
V_{ISO}	* Isolation Breakdown Voltage (R.M.S.)	A.C. 1 minute	2500	V	
T_j	* Operating Junction Temperature		-40 to +125	°C	
T_{stg}	* Storage Temperature		-40 to +125	°C	
	Mounting Torque	Mounting (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)	N·m (kgf·cm)
		Terminal (M8)	Recommended Value 8.8-10 (90-105)	11 (115)	
	Mass	Typical Value	510	g	

Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max.	at V_{DRM} , Single phase, half wave, $T_j=125^\circ\text{C}$	50	mA
I_{RRM}	* Repetitive Peak Reverse Current, max.	at V_{DRM} , Single phase, half wave, $T_j=125^\circ\text{C}$	50	mA
V_{TM}	* Peak On-State Voltage, max.	On-State Current 750A, $T_j=125^\circ\text{C}$ Inst. measurement	1.50	V
I_{GT}/V_{GT}	Gate Trigger Current/Voltage, max.	$T_j=25^\circ\text{C}$, $I_T=1\text{A}$, $V_D=6\text{V}$	100/3	mA/V
V_{GD}	Non-Trigger Gate, Voltage, min.	$T_j=125^\circ\text{C}$, $V_D=1/2V_{DRM}$	0.25	V
t_{gt}	Turn On Time, max.	$I_T=250\text{A}$, $I_G=100\text{mA}$, $T_j=25^\circ\text{C}$, $V_D=1/2V_{DRM}$, $dI_G/dt=0.1\text{A}/\mu\text{s}$	10	μ s
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_j=125^\circ\text{C}$, $V_D=2/3V_{DRM}$, Exponential wave.	500	V/ μ s
I_H	Holding Current, typ.	$T_j=25^\circ\text{C}$	50	mA
I_L	Latching Current, typ.	$T_j=25^\circ\text{C}$	100	mA
$R_{th(j-c)}$	* Thermal Impedance, max.	Junction to case	0.18	°C/W

* mark : Thyristor and Diode part. No mark : Thyristor part

